

Hyperfast power diode - Bare die

Rev.01 - 11 January 2021

**Product data sheet** 

### 1. General description

Hyperfast power diode (Bare die with sawn).

### 2. Features and benefits

- Low Forward Voltage Drop
- Low leakage current
- Fast reverse recovery
- Bare die

### 3. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>RRM</sub> *	repetitive peak reverse voltage			-	-	1200	V
I <sub>F(AV)</sub> **	average forward current	$\delta$ = 0.5; square-wave pulse		-	-	30	А
Static characteristics							
V <sub>F</sub> **	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C		-	2.7	3.5	V
Dynamic characteristics							
t <sub>rr</sub> **	reverse recovery time	$I_{\text{F}}$ = 1 A; $V_{\text{R}}$ = 30 V; $dI_{\text{F}}/dt$ = 100 A/µs; $T_{\text{j}}$ = 25 °C		-	-	65	ns

### 4. Ordering information

Table 2. Ordering information							
	Type number	Orderable part number	Name	Description	Version		
	WBSF30FC120AL	WBSF30FC120ALV	Wafer	Sawn wafer with frame, vacuum packing	Die		

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### 5. Limiting values

#### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>RRM</sub> *	repetitive peak reverse voltage		-	1200	V
V <sub>RWM</sub> *	crest working reverse voltage		-	1200	V
V <sub>R</sub> *	reverse voltage	DC	-	1200	V
I <sub>F(AV)</sub> **	average forward current	$\delta$ = 0.5; square-wave pulse	-	30	А
I <sub>FRM</sub> **	repetitive peak forward current	$\delta$ = 0.5; $t_{\rm p}$ = 25 $\mu s;$ square-wave pulse	-	60	А
I <sub>FSM</sub> **	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	270	A
		$t_{\rm p}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse	-	300	A
T <sub>stg</sub> **	storage temperature		-65	175	°C
T <sub>j</sub> **	junction temperature			175	°C

### 6. Characteristics

Table 4. Cl	haracteristics						
Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
Static cha	aracteristics						
V <sub>F</sub> *	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C	-		2.7	3.5	V
V <sub>F</sub> **	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C	-		2.1	-	V
l <sub>R</sub> *	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-		-	250	μA
l <sub>R</sub> **	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C	-		-	1000	μA
Dynamic	characteristics						
t <sub>rr</sub> ** re	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}$	-		-	65	ns
		$I_F = 30 \text{ A}; \text{ V}_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}$	-		70	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}$	-		153	-	ns
		$I_F = 30 \text{ A}; \text{ V}_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 150 \text{ °C}$	-		173	-	ns

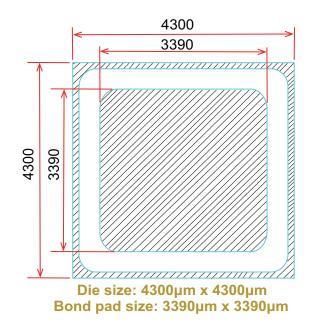
#### Notes:

(1) \* mean that parameter are 100% test at  $T_{amb} = 25^{\circ}C$ (2) \*\* means that the guaranteed ratings and parameter limits will depend on the assembled structure. When correctly assembled with suitable die bonding and wire bonding, the device will have ratings and characteristics guaranteed in this data sheet, similar to the assembled devices BYC30-1200P / BYC30W-1200P.

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MECHANICAL PATAMETER			
Chip size	4.3 x 4.3	mm <sup>2</sup>	
Anode pad size	3.39 x 3.39	mm <sup>2</sup>	
Area total / active	18.49 / 11.49	mm <sup>2</sup>	
Thickness	300	μm	
Wafer size	125	mm	
Max possible chips per wafer	561	pcs	
Passivation	P.E.C.V.D./ Planar		
Front metal	Al		
Back metal	Ti Ni Ag		

#### **CHIP LAYOUT**



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### 7. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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